



Optics for EUV Lithography

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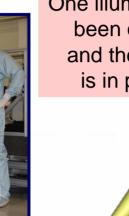
EUV alpha demo tool: Status at Zeiss

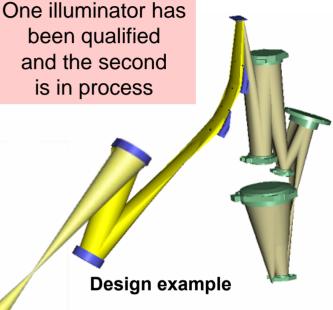
Key specifications

13.5 nm λ NA 0.25 Resolution 50 nm 26x33 mm² field

Magnification 4x







The early projection optics is in the qualification phase



A collector module has been qualifed and is used to test the illuminator at wavelength.

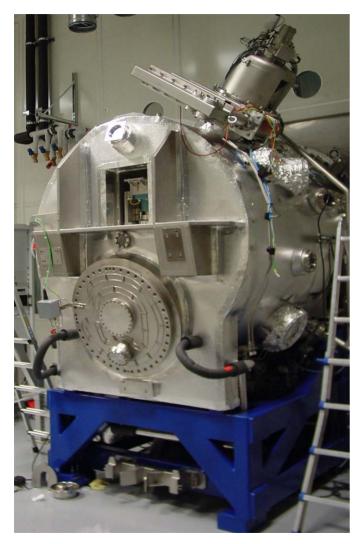
N. Harned et al: this conference

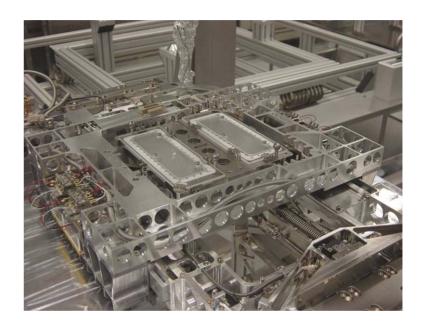
Illuminator



EUV qualification: hardware





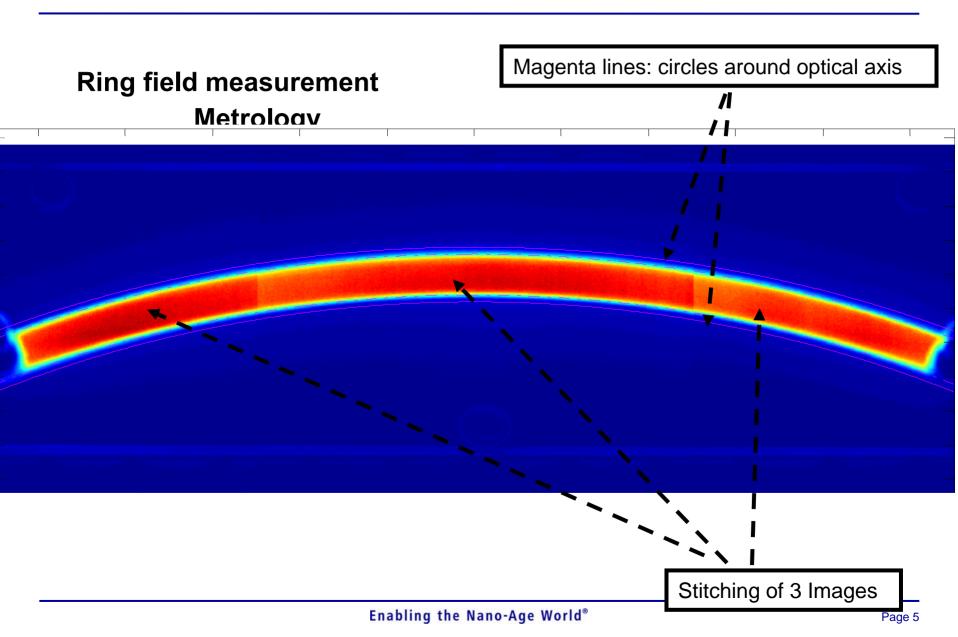


"reticle stage" for metrology

@ λ illuminator metrology tool

EUV qualification: Results (1)

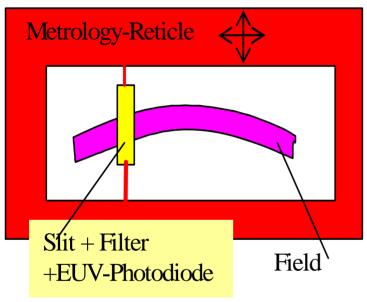






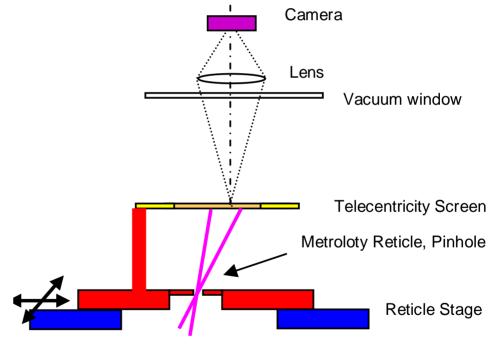
EUV qualification: concept for field and pupil qualification

Setup for Field Qualification

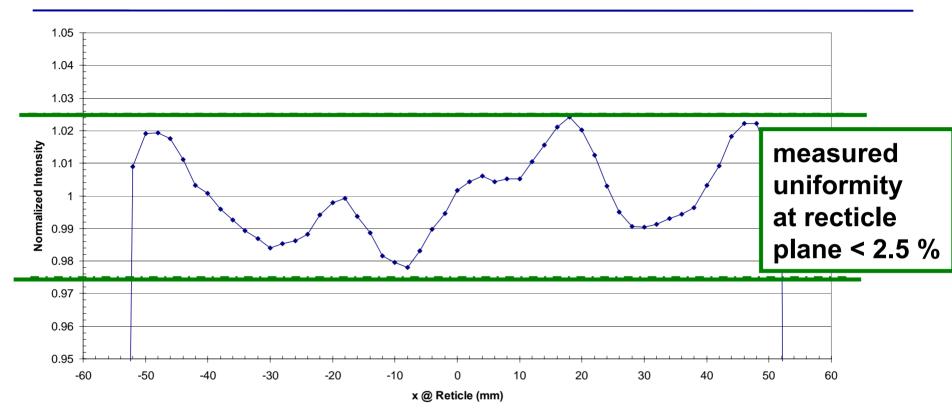


Scanning field with slit EUV photodiode. Integration in y-direction.

Setup for Pupil Qualification



EUV qualification: Results (2)

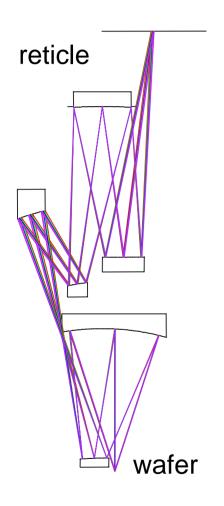


Pupil: Telecentricity < 0.5%

Ellipticity < 10% (calculated value for Sn source)

Projection Optics Box





Status:

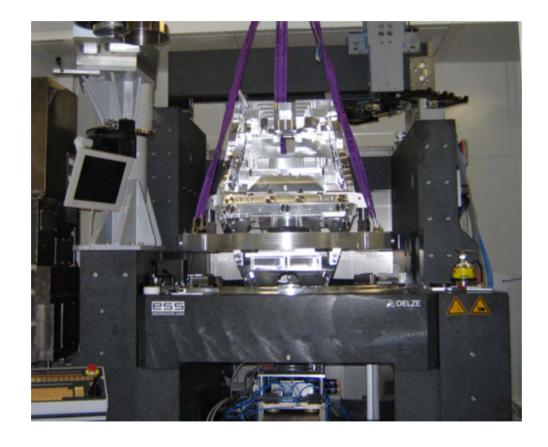
- all mirrors fabricated and coated
- assembly complete
- system metrology has been set up
- the POBox is in the qualification phase

Design example

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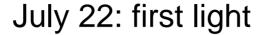
Status POBox: System Metrology

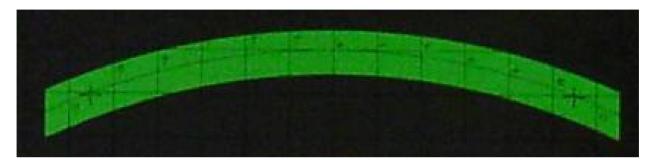
System Metrology for POBox alignment/qualification has been set up



POBox test lens on system inteferometer

Early POBox: Alignment Status





248nm illumination (*converted by phosphor screen): image of the reticle mask in the wafer plane

Status today:

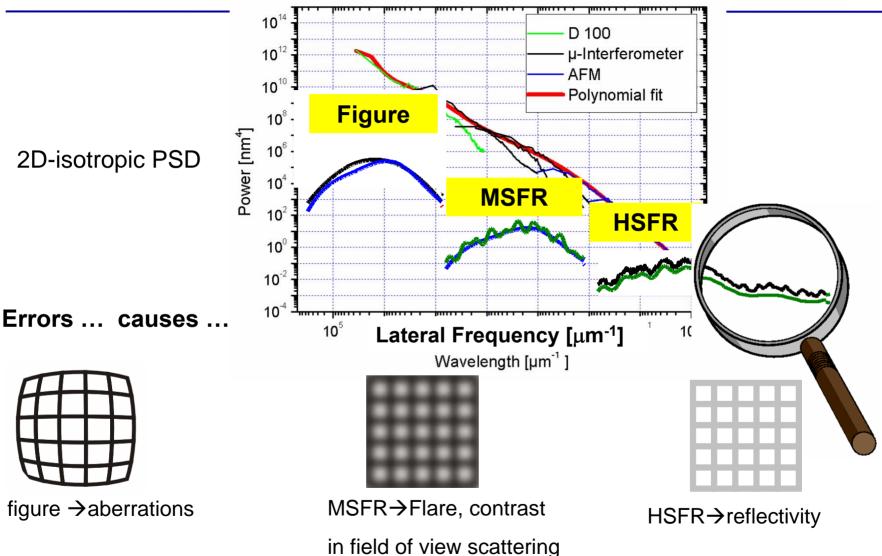
POBox is in the final qualification phase

Performance prediction:

50 nm dense lines can be printed with the early POBox



Optics Technology (1): Fabrication of EUV mirrors



Challenge:

reach about 0.2 nm rms for Figure, MSFR and HSFR simultaneously

Main challenge: flare reduction



Total integrated scatter
$$TIS = (4\pi)^2 \left(\frac{rms_{surface}}{\lambda}\right)^2$$

Due to the very small wavelength EUV imaging is sensitive to scatter !!!

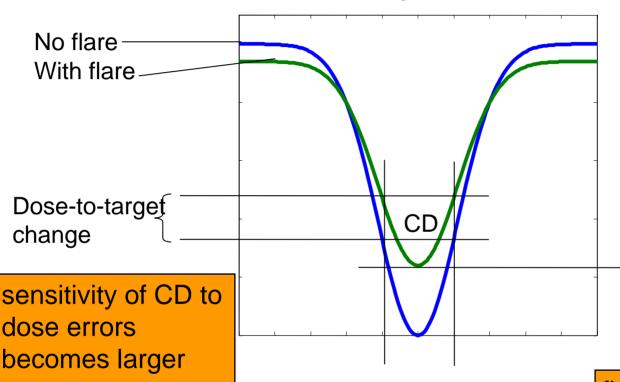
$$TIS \propto n_{mirrors} \cdot rms_{surface}^2$$

Reduction of mid spatial frequency rms is essential to reduce the flare level



Main challenge: flare reduction



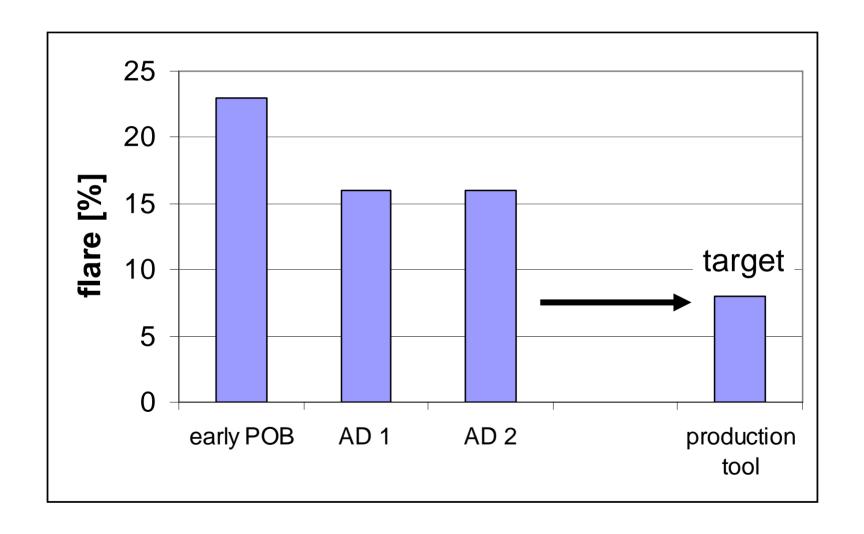


largest impact of flare on isolated features on brightfield masks

proximity effects in dependence of the local reticle transmission

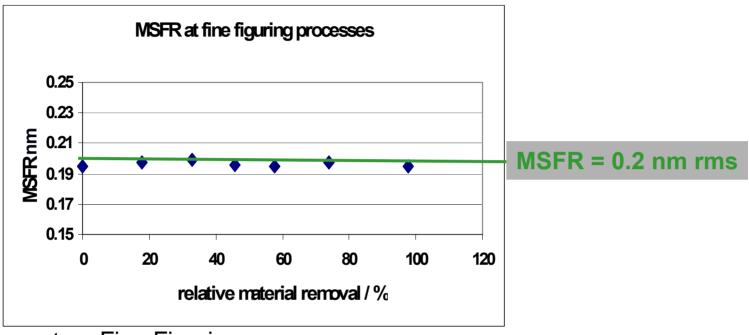
flare reduces overlap of process windows due to dose offsets

Flare roadmap





EUV mirror fabrication: Process development



Critical process step: Fine Figuring

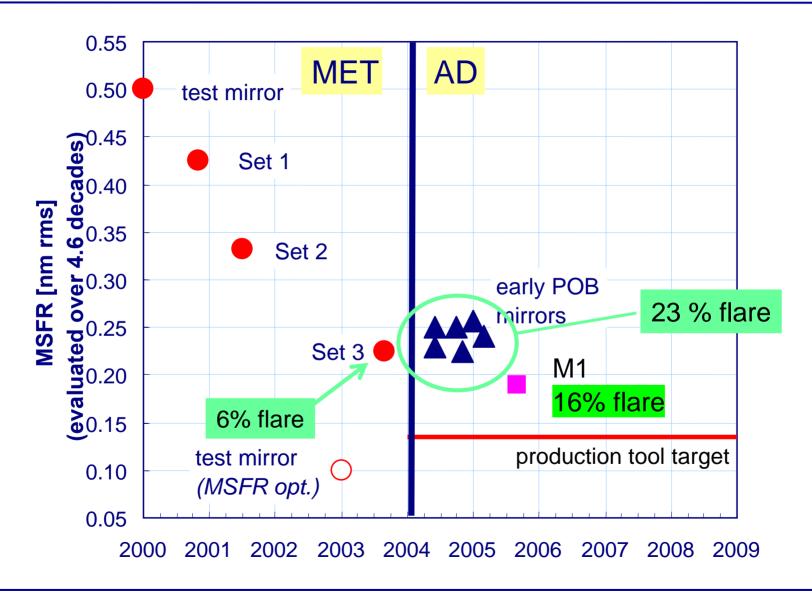
Relative material removal: 100% is representative for reaching figure spec on alpha demo tool mirror

→ technology to reach MSFR of ≤ 0.2 nm rms on alpha tool mirrors has been established (16% flare tool)

→ Mirror for 16% flare tool: M1 - 0.19 nm



Learning curve – mid spatial frequency roughness



Optics Technoloy (2): Coatings

A complete set of alpha tool mirrors has been coated at FOM...



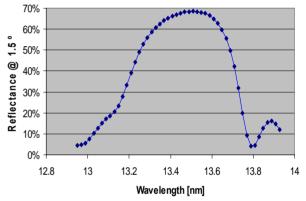
... and Zeiss







Recent development at FOM



New capping layer:

→ reflectance 68.5% comparable to uncapped multilayer

E. Louis et al: this conference

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Summary

- alpha tool program is progressing:
 - illuminator
 - alignment and EUV qualification has been finished
 - POBox
 - all mirrors have been fabricated and coated
 - system metrology for the POBox is operational
 - the POBox has been assembled and is in the qualification phase
 - technology development
 - 16% flare capability has been demonstrated on AD tool mirrors
 - new high reflectivity cap layer has been developed

EUV Optical Technology at Carl Zeiss SMT AG:

- \rightarrow has reached α -tool specs
- is progressing towards production tool capability

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Acknowledgment

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- PTB-BESSY
- Philips
- The teams at ASML and Zeiss
- ...and many others

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GEFÖRDERT VOM

